

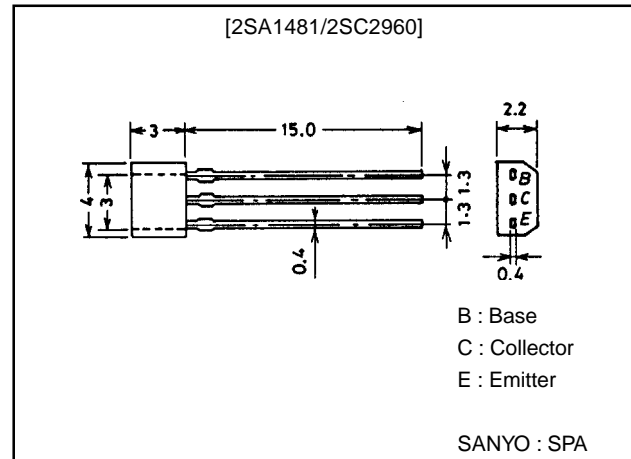
2SA1481/2SC2960**High-Speed Switching Applications****Features**

- Fast switching speed.
- High breakdown voltage.

Package Dimensions

unit:mm

2033



() : 2SA1481

Specifications**Absolute Maximum Ratings at Ta = 25°C**

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CB0}		(-)60	V
Collector-to-Emitter Voltage	V_{CEO}		(-)50	V
Emitter-to-Base Voltage	V_{EBO}		(-)5	V
Collector Current	I_C		(-)150	mA
Peak Collector Current	I_{CP}		(-)400	mA
Collector Dissipation	P_C		250	mW
Junction Temperature	T_J		150	°C
Storage Temperature	T_{stg}		-55 to +150	°C

Electrical Characteristic at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	$V_{CB} = (-)400V, I_E = 0$			(-)0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = (-)4V, I_C = 0$			(-)0.1	μA
DC Current Gain	h_{FE}	$V_{CE} = (-)6V, I_C = (-)1mA$	100*		560*	
Gain-Bandwidth Product	f_T	$V_{CE} = (-)6V, I_C = (-)1mA$		100		MHz
Output Capacitance	C_{ob}	$V_{CB} = (-)6V, f = 1MHz$		2.7		pF
				(4.0)		pF
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = (-)10mA, I_B = (-)1mA$		(-)0.1	(-)0.4	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = (-)10mA, I_B = (-)1mA$		(-)0.75	(-)1.1	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = (-)10\mu A, I_E = 0$	(-)60			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (-)1mA, R_{BE} = \infty$	(-)50			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = (-)10\mu A, I_C = 0$	(-)5			V
Delay Time	t_d	See specified Test Circuit		40	60	ns
Rise Time	t_r	See specified Test Circuit		80	130	ns
				(120)	(230)	ns
Storage Time	t_{stg}	See specified Test Circuit		230	450	ns
				(190)	(700)	ns
Fall Time	t_f	See specified Test Circuit		160	250	ns
				(240)	(390)	ns

* ; The 2SA1481/2SC2960 are classified by 1mA h_{FE} as follows :

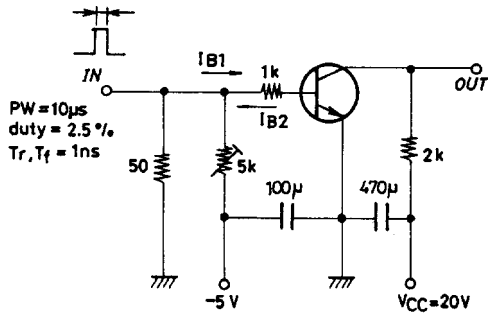
100 E	200	160 F	320	280 G	560
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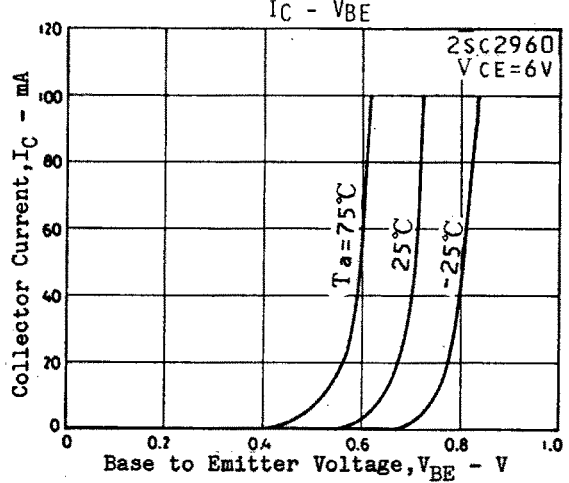
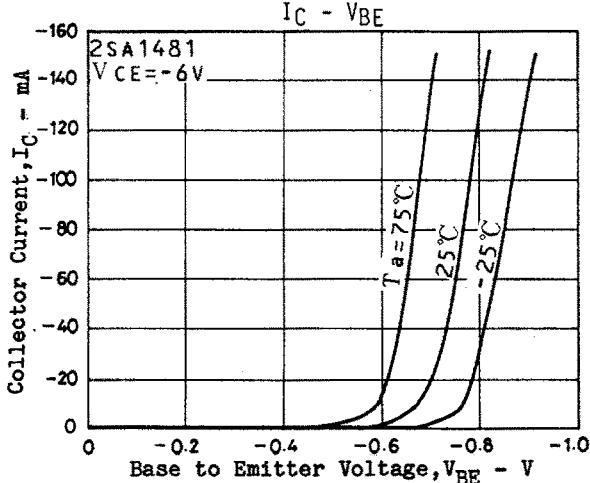
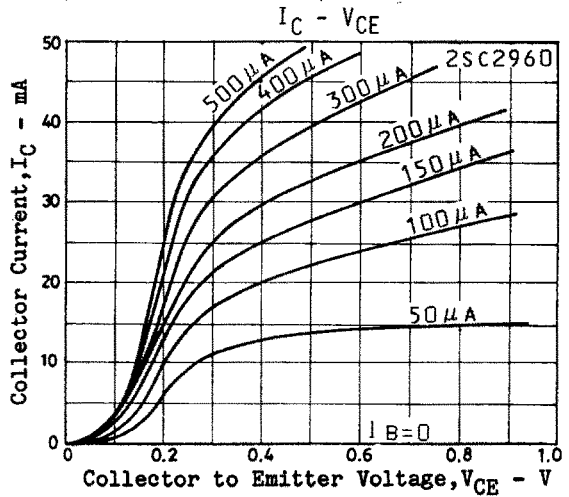
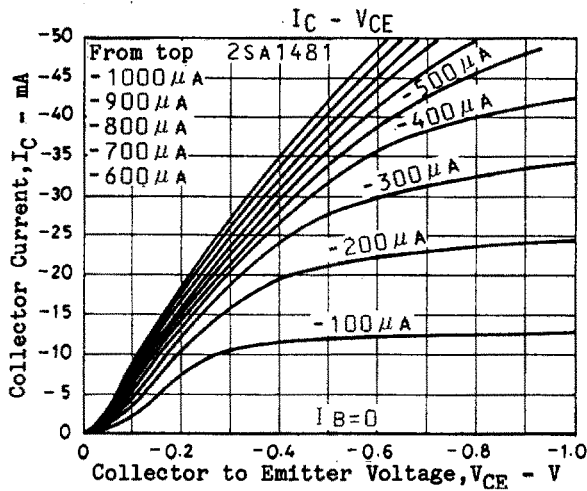
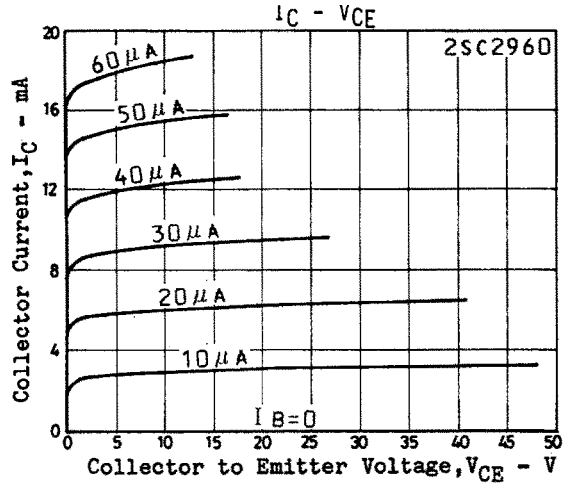
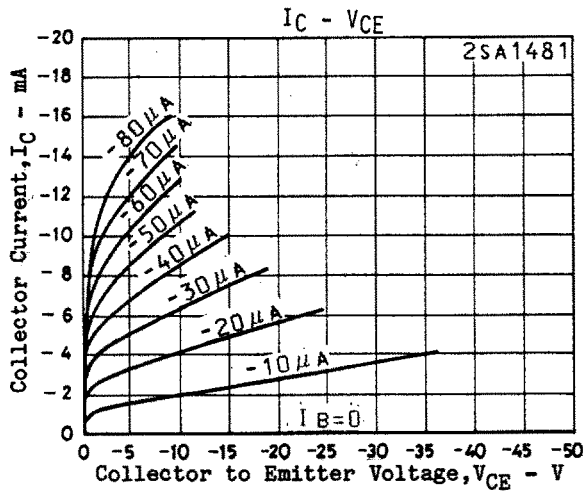
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Switching Time Test Circuit

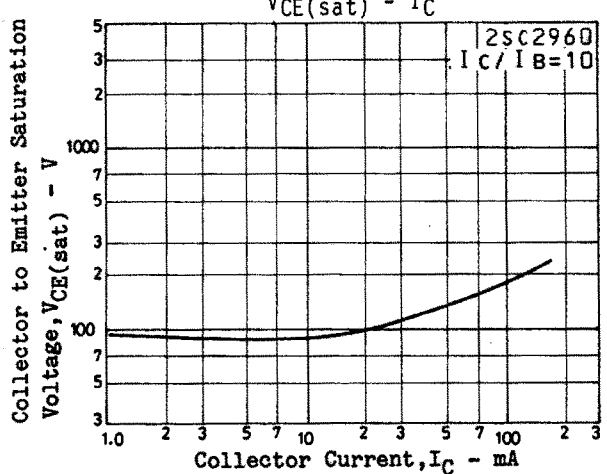
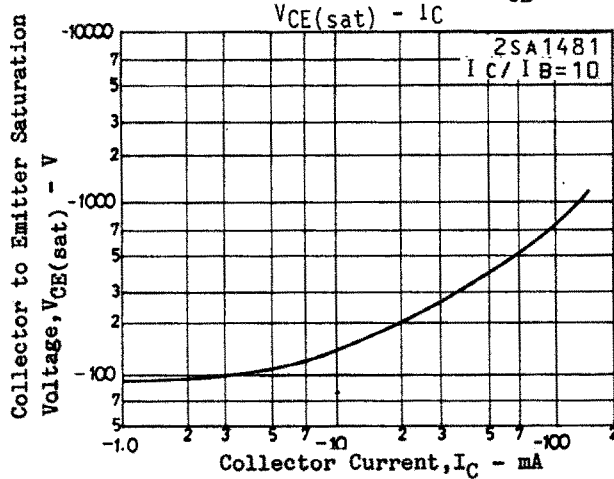
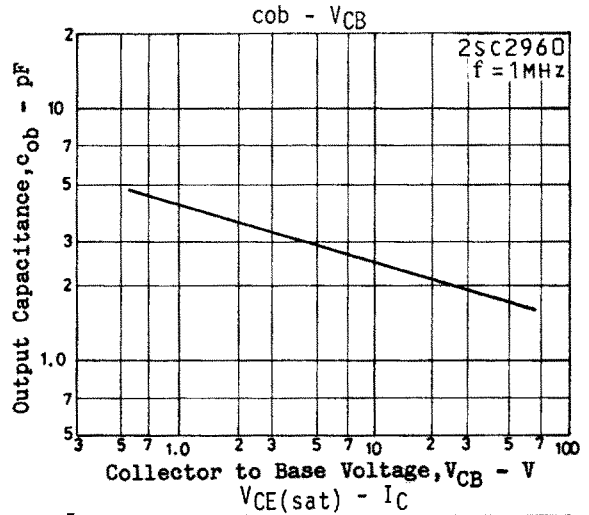
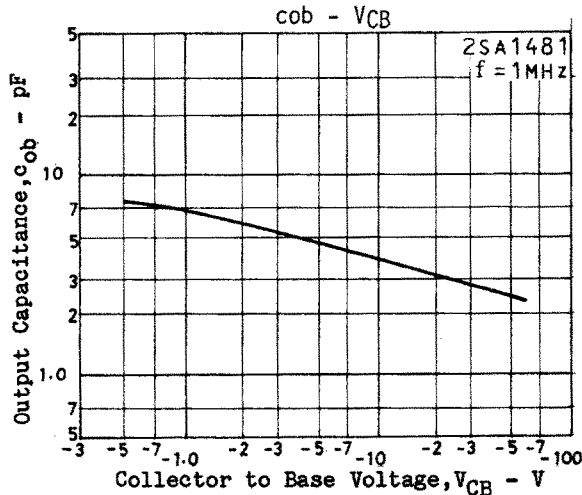
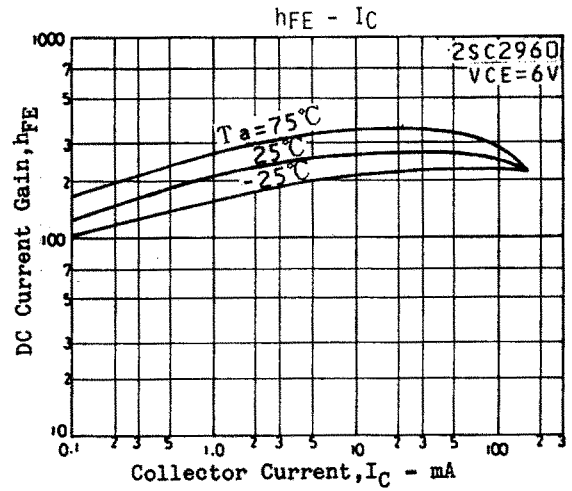
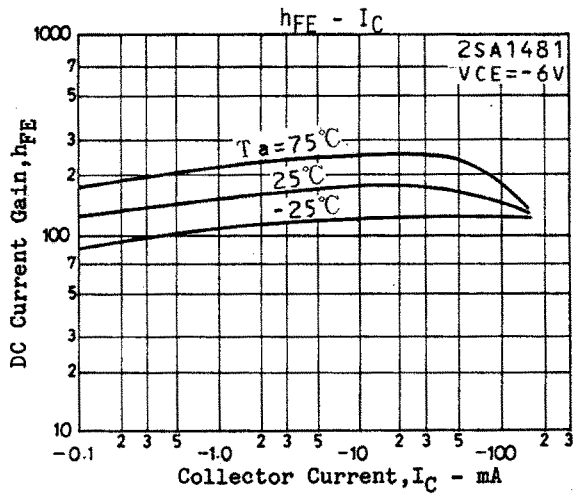
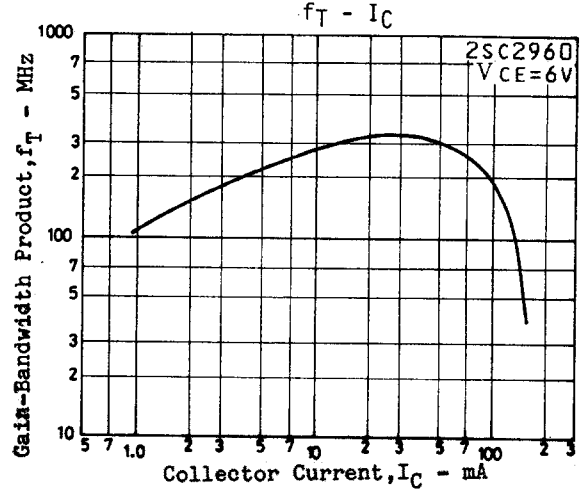
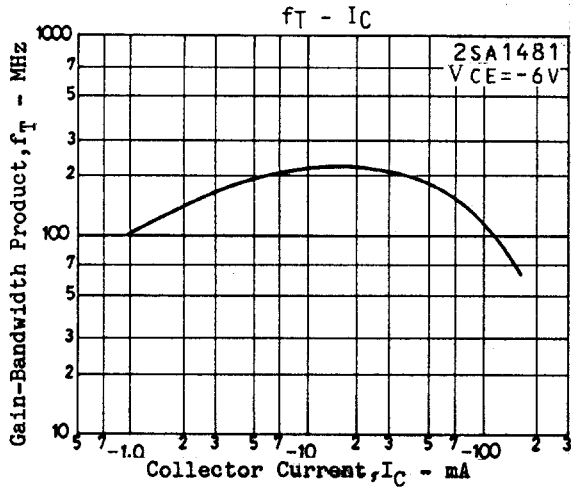
(For PNP, the polarity is reversed.)



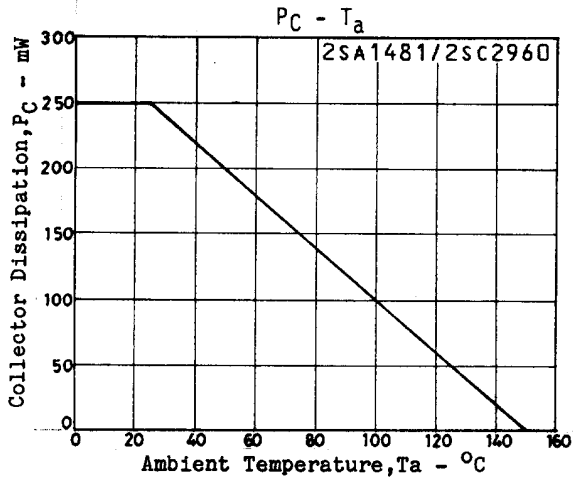
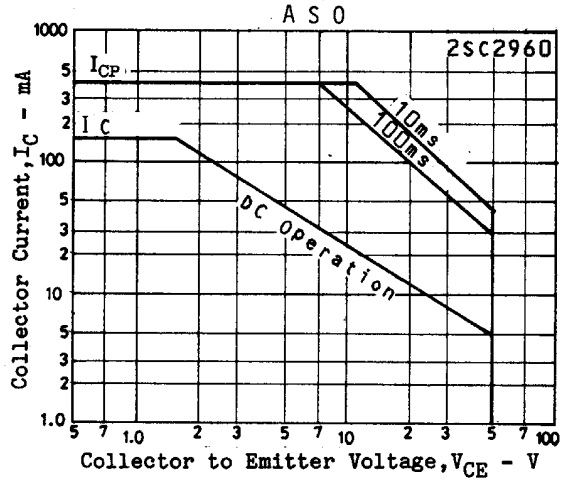
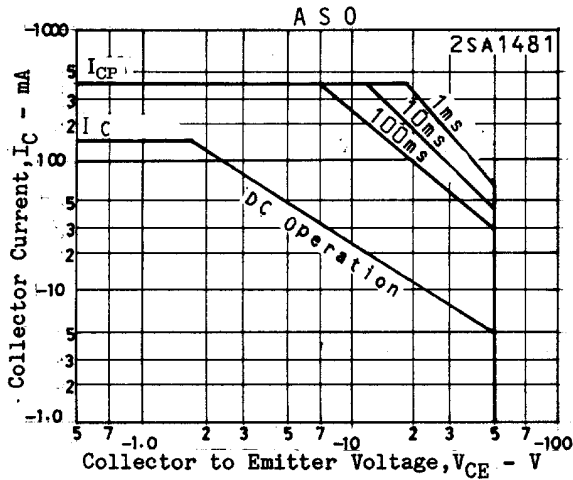
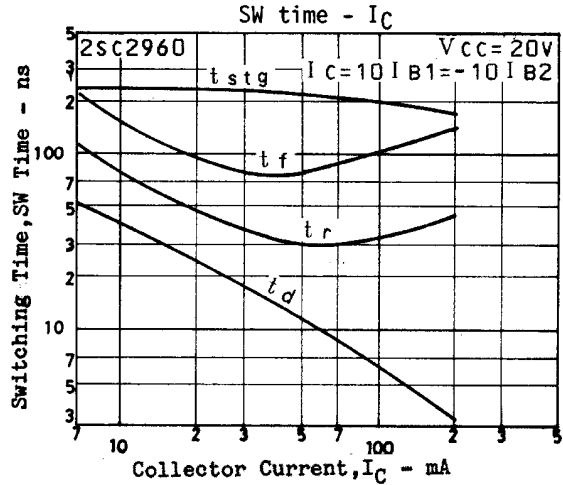
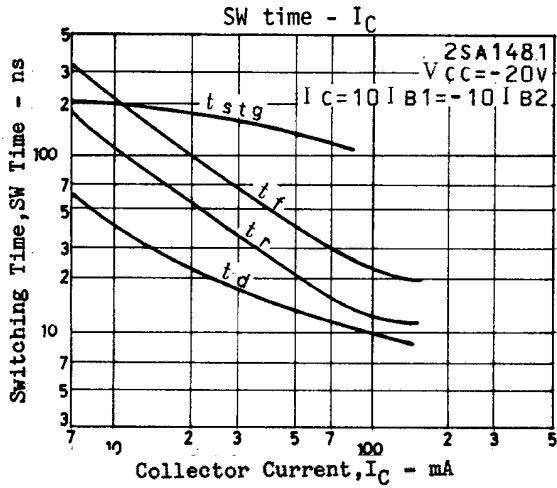
$10 I_{B1} = -10 I_{B2} = I_C = 10 \text{ mA}$
Unit (resistance : Ω , capacitance : F)



2SA1481/2SC2960



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